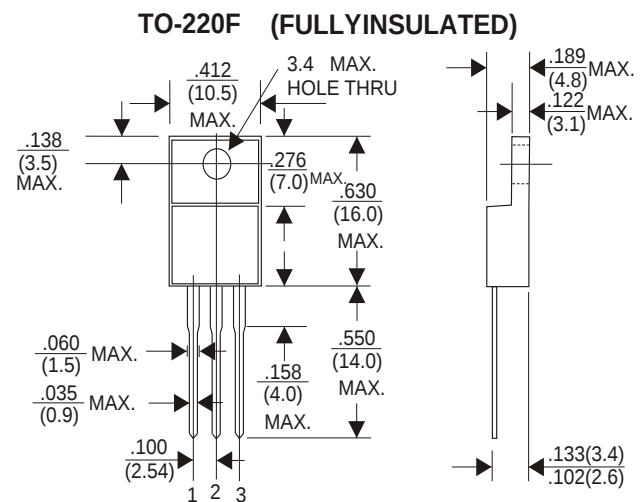
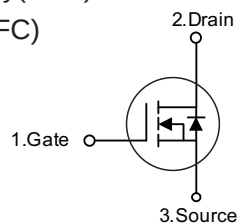


Features

- 650V,16A
- $R_{DS(ON)} = 0.48\Omega$ (Typ.) @ $V_{GS} = 10V$, $I_D = 8A$
- Fast Switching
- Improved dv/dt Capability
- 100% Avalanche Tested

Application

- Switch Mode Power Supply(SMPS)
- Uninterruptible Power Supply(UPS)
- Power Factor Correction (PFC)



Dimensions in inches and (millimeters)

Absolute Maximum Ratings ($T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter		Max.	Units
V_{DSS}	Drain-Source Voltage		650	V
V_{GSS}	Gate-Source Voltage		± 30	V
I_D	Continuous Drain Current	$T_C = 25$	16	A
		$T_C = 100$	10	A
I_{DM}	Pulsed Drain Current ^{note1}		64	A
E_{AS}	Single Pulsed Avalanche Energy ^{note2}		461	mJ
P_D	Power Dissipation	$T_C = 25$	98	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case		1.3	/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient		62.5	/W
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	

16N65F

Electrical Characteristics (T_J=25 unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	650	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =650V, V _{GS} =0V, T _J =25	-	-	1	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} = ±30V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	2	3	4	V
R _{DS(on)}	Static Drain-Source on-Resistance note3	V _{GS} =10V, I _D =8A	-	0.48	0.55	Ω
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =25V, V _{GS} =0V, f=1.0MHz	-	2740	-	pF
C _{oss}	Output Capacitance		-	214	-	pF
C _{rss}	Reverse Transfer Capacitance		-	15	-	pF
Q _g	Total Gate Charge	V _{DD} =520V, I _D =16A, V _{GS} =10V	-	71	-	nC
Q _{gs}	Gate-Source Charge		-	10	-	nC
Q _{gd}	Gate-Drain(“Miller”) Charge		-	32	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DD} =325V, I _D =16A, R _G =25Ω	-	35	-	ns
t _r	Turn-on Rise Time		-	50	-	ns
t _{d(off)}	Turn-off Delay Time		-	160	-	ns
t _f	Turn-off Fall Time		-	65	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	16	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	64	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _{SD} =16A	-	-	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} =0V, I _S =16A,	-	430	-	ns
Q _{rr}	Reverse Recovery Charge	di/dt=100A/μs	-	6.5	-	μC

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition: T_J = 25°C, V_{DD} = 80V, V_G = 10V, L= 10mH, I_{AS} = 9.6A

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤1%

RATING AND CHARACTERISTIC CURVES (16N65F)

Figure1: Output Characteristics

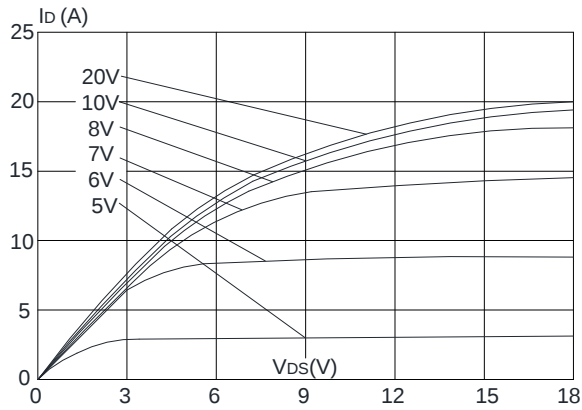


Figure 2: Typical Transfer Characteristics

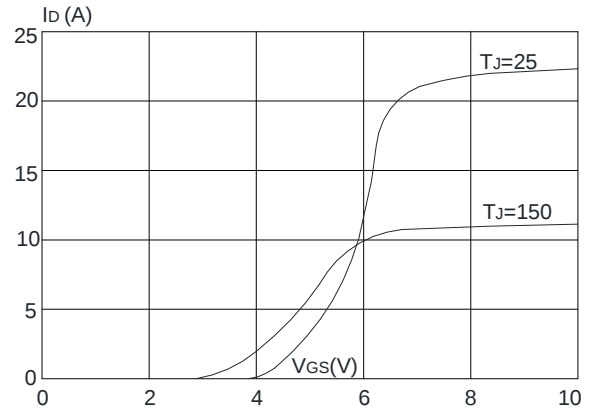


Figure 3: On-resistance vs. Drain Current

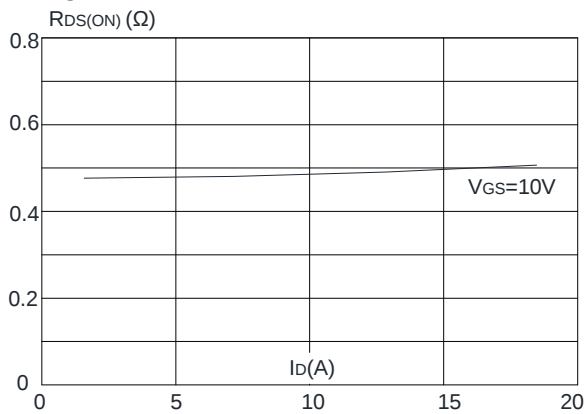


Figure 4: Body Diode Characteristics

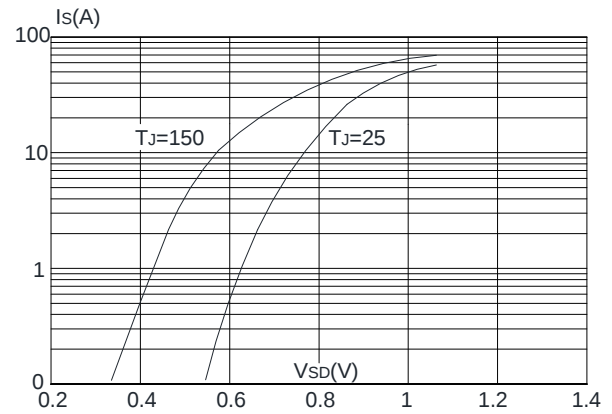


Figure 5: Gate Charge Characteristics

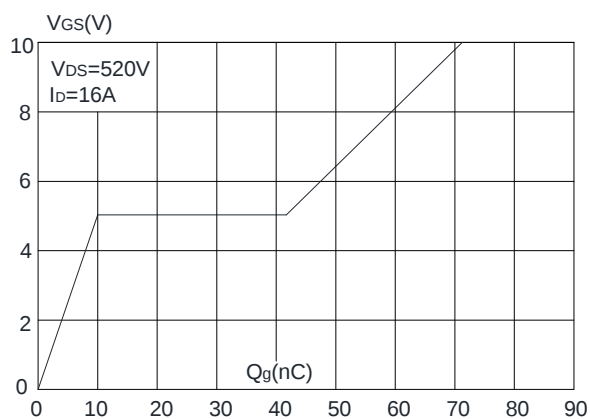
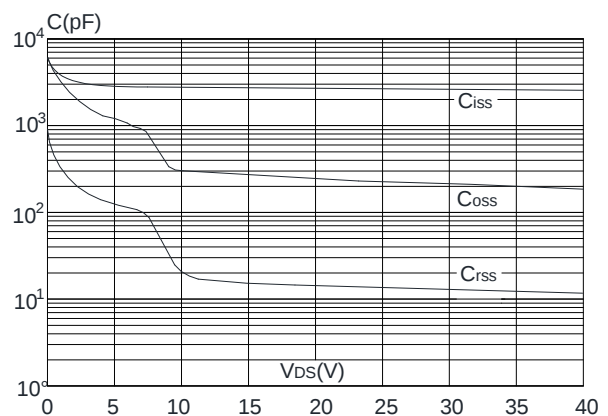


Figure 6: Capacitance Characteristics



RATING AND CHARACTERISTIC CURVES (16N65F)

Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

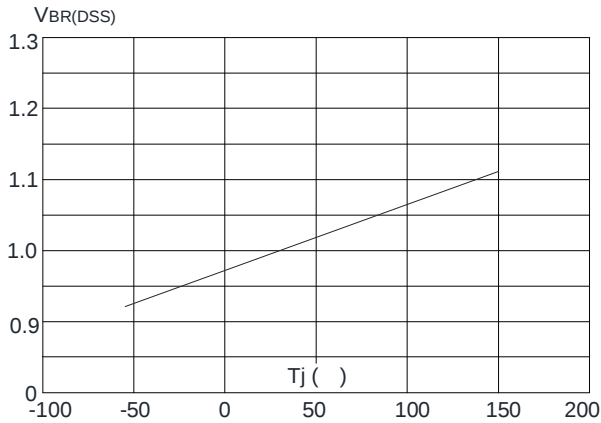


Figure 8: Normalized on Resistance vs. Junction Temperature

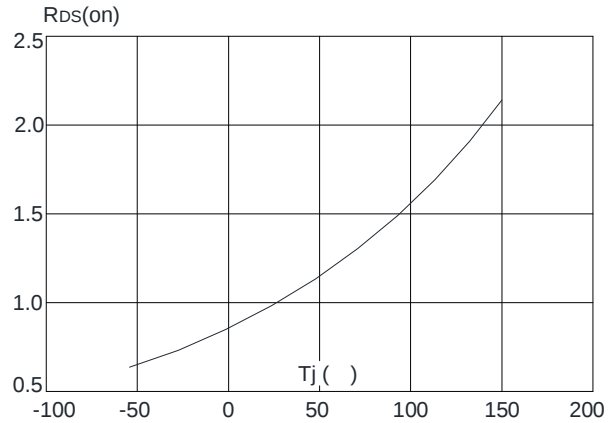


Figure 9: Maximum Safe Operating Area

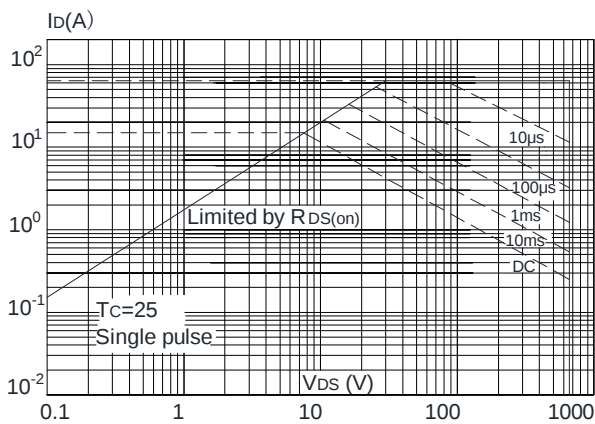


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

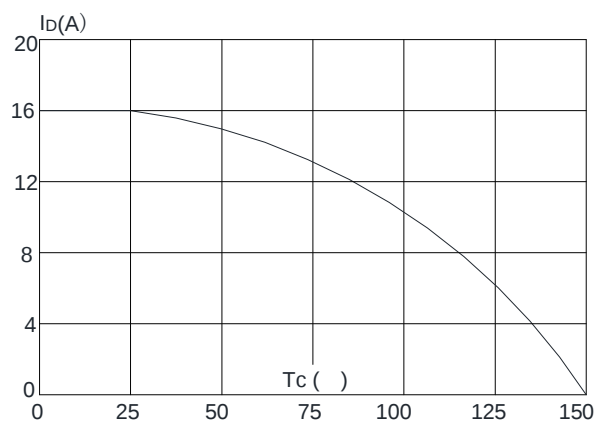


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case

